# Panasonic

Zener Diode

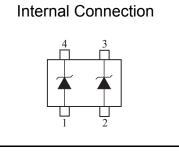
DZ4J100K0R Silicon epitaxial planar type

#### Unit: mm 2.0 For constant voltage / For surge absorption circuit <u>0. 3</u> 0 13 4 Features Excellent rising characteristics of zener current Iz 25 Low zener operating resistance Rz Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant) 2 1 0.7 Marking Symbol: NJ (0.65)(0.65) Basic Part Number : 1.3 Dual DZ2J100 (Parallel) Packaging 3. Cathode-2 1. Anode-1 Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard) 4. Cathode-1 2. Anode-2 Panasonic SMini4-F3-B Absolute Maximum Ratings Ta = 25 °C JEITA SC-113BB Parameter Unit Code Symbol Rating

Repetitive peak forward current	IFRIVI	200	mA
Total power dissipation <sup>*1</sup>	PT	200	mW
Electrostatic discharge *2	ESD	±8	kV
Junction temperature	Tj	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	°C

Note) \*1: Mounted on glass epoxy print board. (45 mm x 45 mm x 1 mm) Solder in (0.8 mm x 0.8 mm)

\*2: Test method:IEC61000\_4\_2(C = 150 pF,R = 330 Ω, Contact discharge:10 times)



### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	VF	IF = 10 mA			1.0	V
Zener voltage <sup>*1, *2</sup>	VZ	IZ = 5 mA	9.50		10.50	V
Zener operating resistance	RZ	IZ = 5 mA			30	Ω
Zener rise operating resistance	RZK	IZ = 0.5 mA			60	Ω
Reverse current	IR	VR = 7 V			0.05	μA
Temperature coefficient of zener voltage *3	SZ	IZ = 5 mA		7.2		mV/°C

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. Absolute frequency of input and output is 5 MHz.

 \*1: The temperature must be controlled 25 °C for VZ mesurement. VZ value measured at other temperature must be adjusted to VZ (25 °C)

vz value measured at other temperature must be adjusted to vz (25 C)

\*2: VZ guaranted 20 ms after current flow.

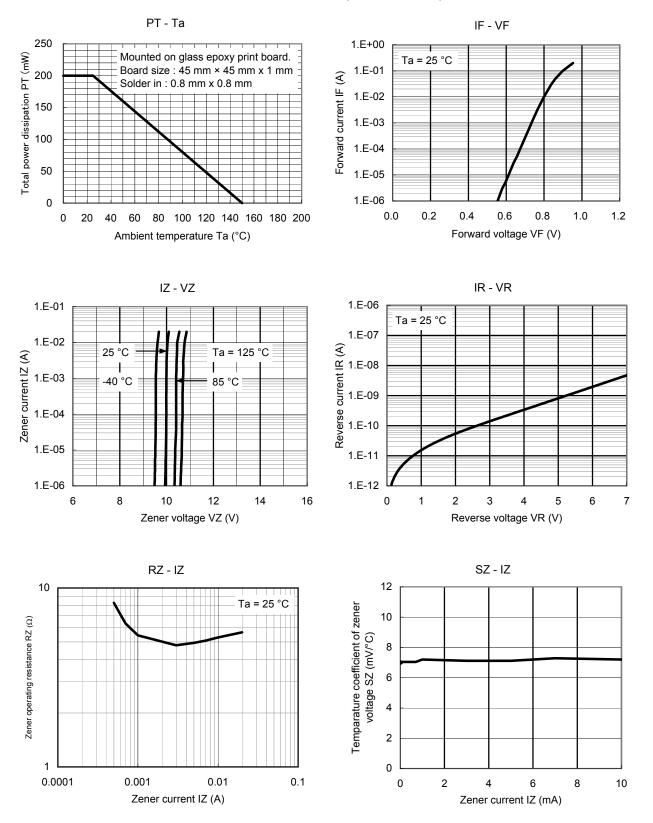
\*3: Tj = 25 °C to 150 °C





Zener Diode DZ4J100K0R

## Technical Data (reference)

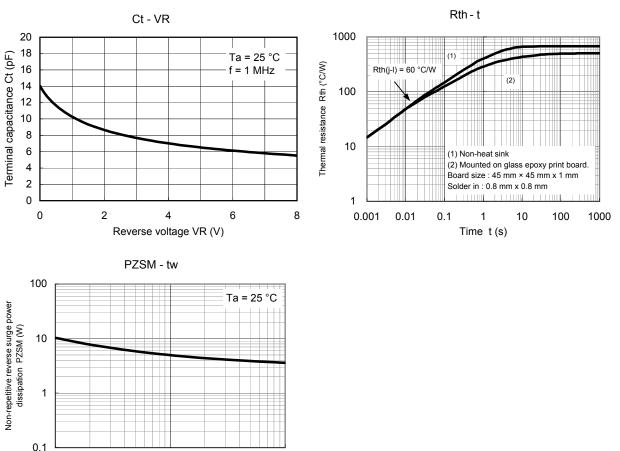


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Established : 2009-12-11 Revised : 2013-10-04



Zener Diode **DZ4J100K0R** 



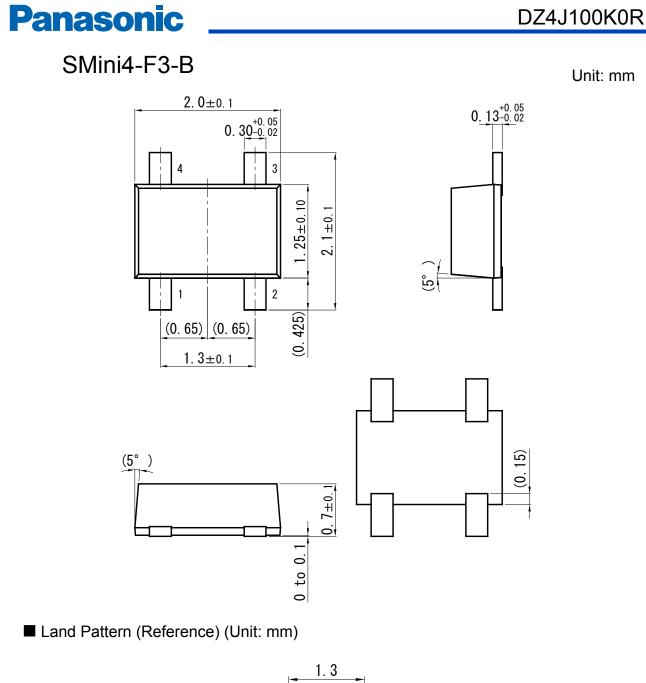
10000

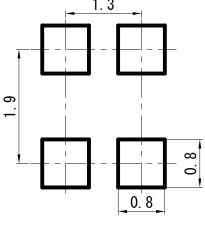
Established : 2009-12-11 : 2013-10-04 Revised

100

1000

Pulse width tw (µs)





Zener Diode

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